

# Product Change Notification: SYST-31DFAZ397

# Date:

02-Apr-2025

# **Product Category:**

High-Side Current Sense Amplifiers

# **Notification Subject:**

Data Sheet - MCP6C26 - Zero-Drift, 36V High-Side Current Sense Amplifier

# Affected CPNs:

SYST-31DFAZ397\_Affected\_CPN\_04022025.pdf SYST-31DFAZ397\_Affected\_CPN\_04022025.csv

# Notification Text:

#### SYST-31DFAZ397

Microchip has released a new Datasheet for the MCP6C26 - Zero-Drift, 36V High-Side Current Sense Amplifier of devices. If you are using one of these devices please read the document located at MCP6C26 - Zero-Drift, 36V High-Side Current Sense Amplifier.

Notification Status: Final

**Description of Change:** 

- Updated Table 1-1.
- Updated Section 2.5, Time Response.

Impacts to Data Sheet: See above details.

Reason for Change: To improve productivity.

Change Implementation Status: Complete

Date Document Changes Effective: 02 Apr 2025

**NOTE:** Please be advised that this is a change to the document only the product has not been

changed.

Markings to Distinguish Revised from Unrevised Devices: N/A

# Attachments:

MCP6C26 - Zero-Drift, 36V High-Side Current Sense Amplifier

Please contact your local Microchip sales office with questions or concerns regarding this notification.

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Affected Catalog Part Numbers (CPN)

MCP6C26T-050E/LTY

MCP6C26T-100E/LTY

MCP6C26T-200E/LTY



# **MCP6C26**

# Zero-Drift, 36V Current Sense Amplifier

#### Features

- Single Amplifier: MCP6C26
- Gains: 50, 100 and 200 V/V
- Bidirectional or Unidirectional
- Input ("Common Mode") Voltages:
  - -0.2V to +36V, Specified
  - -5V to +39.5V, Survival
- · Power Supply
  - 2.7V to 5.5V
  - Single or Dual (Split) Supplies
- · High DC Precision
  - V<sub>OS</sub>: ±15 μV (typical)
  - CMRR: 129 dB (typical at G<sub>DM</sub> = 200)
  - PSRR: 136 dB (typical at  $G_{DM}$  = 200)
  - Gain Error: ±0.05% (typical)
- POR Protection
- LV POR for V<sub>DD</sub>
- Gain-Bandwidth Product: 9 MHz (typical)
- Supply Current
  - $I_{DD} = 65 \,\mu A \,(typical)$
- Specified Temperature Range
  - -40°C to +125°C

#### **Typical Applications**

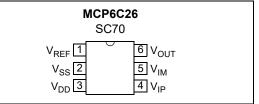
- DC/DC Converters
- · Battery Management
- USB Power Delivery
- Uninterruptible Power Supplies
- Differential Sensor Conditioning

#### **General Description**

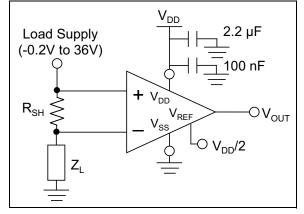
The Microchip Technology Inc. MCP6C26 current sense amplifier is offered with preset gains of 50, 100 and 200 V/V. The input voltage range ( $V_{IP}$  and  $V_{IM}$ ) is -0.2V to +36V. The Differential-Mode input range ( $V_{DM} = V_{IP} - V_{IM}$ ) supports unidirectional and bidirectional applications. The power supply can be set between 2.7V and 5.5V. Parts come in an SC70 package and are specified over the -40°C to +125°C (E-Temp) range.

The architecture includes an internal Zero-Drift op amp and precision internal resistors. It supports very low input errors and allows current sense designs to use shunt resistors of lower value (with lower power dissipation).

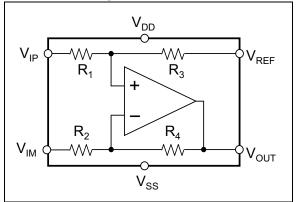
#### Package Types (Top View)



#### **Typical Application Circuit**



#### **Functional Diagram**



## **Gain Options**

Table 1 shows key specifications that differentiate between the three different differential gain ( $G_{DM}$ ) options. See Section 1.0 "Electrical Characteristics", Section 6.0 "Packaging Information" and the Product Identification System for further information on the  $G_{DM}$  options available.

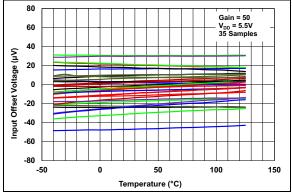
#### TABLE 1:KEY DIFFERENTIATING SPECIFICATIONS

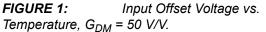
Part No.	G <sub>DM</sub> (V/V) Nom.	9 <sub>E</sub> (±%)	V <sub>OS</sub> (±µV) Max.	TC <sub>1</sub> (±nV/°C) Max. (Note 1)	CMRR (dB) Min. (Note 2)	PSRR (dB) Min.	GBWP (MHz) Typ.	BW (kHz) Typ.
MCP6C26-050	50		90	265	102			180
MCP6C26-100	100	0.5	75	240	102	100	9	90
MCP6C26-200	200		65	225	105			45

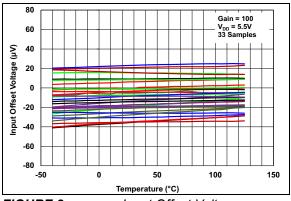
**Note 1:** TC<sub>1</sub> limits are by design and characterization only; not tested in production. TC<sub>1</sub> covers the Extended Temperature Range (-40°C to +125°C or E-Temp).

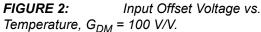
2: The common mode input range is 0V to 36V.

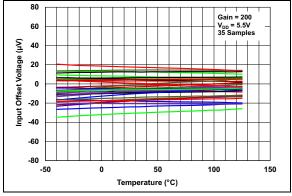
Figure 1, Figure 2 and Figure 3 show input offset voltage versus temperature for the three gain options ( $G_{DM}$  = 50, 100 and 200 V/V).











**FIGURE 3:** Input Offset Voltage vs. Temperature,  $G_{DM} = 200 \text{ V/V}$ .

The MCP6C26's CMRR supports applications in noisy environments. Figure 4 shows how CMRR is high, even for frequencies near 100 kHz.

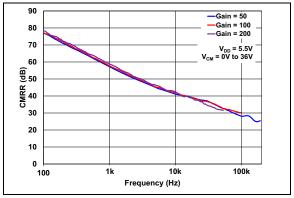


FIGURE 4:

CMRR vs. Frequency.

# 1.0 ELECTRICAL CHARACTERISTICS

# 1.1 Absolute Maximum Ratings †

V <sub>DD</sub> - V <sub>SS</sub>	0V to +6.0V
Current at Input Pins (Note 1)	±2 mA
Analog Inputs (V <sub>IP</sub> and V <sub>IM</sub> ) (Note 1)(Note 2)	-5.0V to +39.5V
All Other Inputs and Outputs	V <sub>SS</sub> - 0.3V to V <sub>DD</sub> + 0.3V
Input Difference Voltage (V <sub>DM</sub> ) (Note 1)(Note 2)	±39.5V
Output Short-Circuit Current	Continuous
Current at Output and Supply Pins	±30 mA
Storage Temperature	65°C to +150°C
Maximum Junction Temperature (Note 2)	+155°C
ESD protection (HBM, CDM)	≥ 2 kV, 2 kV

**† Notice:** Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at those or any other conditions above those indicated in the operational sections of this specification is not intended. Exposure to maximum rating conditions for extended periods may affect device reliability.

**Note 1:** These voltage and current ratings are physically independent; each required condition must be enforced by the user (see Section 5.1.2 "Input Voltage/Current Limits").

2: This condition is intended for intermittent use only.

#### 1.2 Specifications

#### TABLE 1-1: DC ELECTRICAL CHARACTERISTICS

**Electrical Characteristics**: Unless otherwise indicated,  $T_A = +25^{\circ}C$ ,  $V_{DD} = 2.7V$  to 5.5V,  $V_{SS} = GND$ ,  $V_{CM} = 15V$ ,  $V_{DM} = 0V$ ,  $V_{REF} = V_{DD}/2$ ,  $V_{OUT} = V_{DD}/2$ ,  $V_L = V_{DD}/2$ ,  $R_L = 10 \text{ k}\Omega$  to  $V_L$  and  $C_L = 30 \text{ pF}$ ; see Figure 1-5 and Figure 1-6.

Parameter	Sym.	Min.	Тур.	Max.	Units	Gain	Conditions
Input Offset (V <sub>IP</sub> = V <sub>IM</sub> )							
Input Offset Voltage	V <sub>OS</sub>	-90	±20	90		50	
	_	-75	±15	75	μV	100	
		-65	±15	65		200	
V <sub>OS</sub> Drift,	TC <sub>1</sub>	-265	-35	265		50	T <sub>A</sub> = -40°C to +125°C,
Linear Temp. Co.		-235	-25	235	nV/°C	100	(Note 1, Note 2)
		-225	-20	225		200	
Power Supply	PSRR		126	_	dB	50	V <sub>DD</sub> = 2.7V to 5.5V
Rejection Ratio		100	131			100	
			136			200	
Input Current and Imped	ance (V <sub>IP</sub> a	and V <sub>IM</sub> )					•
V <sub>IP</sub> 's Input Bias Current	I <sub>BP</sub>	20	33	48	μA	All	V <sub>CM</sub> = 15V
V <sub>IM</sub> 's Input Bias Current	I <sub>BM</sub>	20	33	48	μA	All	V <sub>CM</sub> = 15V
Input Common-Mode Vo	tage (V <sub>CM</sub>	)					
Common-Mode Rejection	CMRR	102	120	_	dB	50	V <sub>DD</sub> = 2.7V to 5.5V,
Ratio		102	123			100	V <sub>CM</sub> = 0V to 36V
		105	129			200	
Input Common-Mode Voltage Range (Low)	V <sub>CML</sub>	_	—	-0.2	V	All	
Input Common-Mode Voltage Range (High)	V <sub>CMH</sub>	36	—	—	V	All	
Reference Voltage (V <sub>REF</sub> )	)			1			
Gain Resistance	R <sub>1</sub> , R <sub>2</sub>	_	20	_	kΩ	50	
			10			100	
			5			200	
	R <sub>3</sub> , R <sub>4</sub>	_	1	—	MΩ	All	
Reference Voltage Rejection Ratio	CMRR2	100	125	—	dB	All	V <sub>REF</sub> = 0.2V to 4.8V
V <sub>REF</sub> Voltage Range	V <sub>REF</sub>	-0.2	—	V <sub>DD</sub> +0.2	V	All	
Differential Input (V <sub>DM</sub> )							
Differential Gain	G <sub>DM</sub>		50		V/V	50	MCP6C26-050
			100		1	100	MCP6C26-100
			200		1	200	MCP6C26-200
Differential Gain Error	9 <sub>E</sub>	-0.5	±0.05	+0.5	%	All	
Differential Gain Drift	$\Delta g_E / \Delta T_A$	_	±5	—	ppm/°C	All	$G_{DM}V_{DM} = 2.5V (Note 1)$
Differential Nonlinearity (Note 3)	INL <sub>DM</sub>	—	±100	—	ppm	All	V <sub>DM</sub> = ±10 mV (Note 1)
Differential Voltage (Low)	V <sub>DML</sub>	_	-	(V <sub>SS</sub> -0.2)/G <sub>D</sub> M	V	All	

**Note 1:** Set by design and characterization.

2: See the discussion in Section 1.5.2, Input Offset Related Errors.

3: See Section 1.5, Explanation of DC Error Specifications.

#### TABLE 1-1: DC ELECTRICAL CHARACTERISTICS (CONTINUED)

**Electrical Characteristics**: Unless otherwise indicated,  $T_A = +25^{\circ}C$ ,  $V_{DD} = 2.7V$  to 5.5V,  $V_{SS} = GND$ ,  $V_{CM} = 15V$ ,  $V_{DM} = 0V$ ,  $V_{REF} = V_{DD}/2$ ,  $V_{OUT} = V_{DD}/2$ ,  $V_L = V_{DD}/2$ ,  $R_L = 10 \text{ k}\Omega$  to  $V_L$  and  $C_L = 30 \text{ pF}$ ; see Figure 1-5 and Figure 1-6.

Parameter	Sym.	Min.	Тур.	Max.	Units	Gain	Conditions			
Differential Voltage (High)	V <sub>DMH</sub>	5.7/G <sub>DM</sub>	_	_	V	All				
Output (V <sub>OUT</sub> )										
Minimum Output Voltage Swing	V <sub>OL</sub>	—	45	110	mV	All				
Maximum Output Voltage Swing	V <sub>DD</sub> – V <sub>OH</sub>	—	80	160	mV	All				
Output Short Circuit Current	I <sub>SC</sub>	—	±20	Ι	mA	All				
Power Supplies (V <sub>DD</sub> , V <sub>S</sub>	<sub>S</sub> and V <sub>IP</sub> )									
Low Supply Voltage	V <sub>DD</sub>	2.7	_	5.5	V	All				
Quiescent Current at $V_{SS}$	I <sub>SS</sub>	-150	-120	-90	μA					
Quiescent Current at $V_{DD}$	I <sub>DD</sub>	40	65	90						
POR Trip Voltages,	V <sub>PL</sub>	—	1.9	_	V	All	POR turns off (V <sub>DD</sub> $\downarrow$ )			
Low-Side (V <sub>DD</sub> )	V <sub>PH</sub>		1.95	_			POR turns on (V <sub>DD</sub> $\uparrow$ )			

**Note 1:** Set by design and characterization.

2: See the discussion in Section 1.5.2, Input Offset Related Errors.

3: See Section 1.5, Explanation of DC Error Specifications.

#### TABLE 1-2: AC ELECTRICAL CHARACTERISTICS

**Electrical Characteristics**: Unless otherwise indicated,  $T_A = +25^{\circ}C$ ,  $V_{DD} = 2.7V$  to 5.5V,  $V_{SS} = GND$ ,  $V_{CM} = 15V$ ,  $V_{DM} = 0V$ ,  $V_{REF} = V_{DD}/2$ ,  $V_L = V_{DD}/2$ ,  $R_L = 10 \text{ k}\Omega$  to  $V_L$  and  $C_L = 30 \text{ pF}$ ; see Figure 1-7.

Parameter	Sym.	Min.	Тур.	Max.	Units	Gain	Conditions
AC Response					1		•
Bandwidth	BW	_	180		kHz	50	$G_{DM}V_{DM} = 0.1V_{p-p}$
		_	90	_		100	
			45			200	
V <sub>DM</sub> Slew Rate	SR	—	1.3	_	V/µs	All	$G_{DM}V_{DM}$ Step = $V_{DD} - 0.5V$
Noise							
Input Noise Voltage		—	42	—	nV/√Hz	50	f = 1 kHz (Note 1)
Density	e <sub>ni</sub>	—	36	_		100	
			32	—		200	
Power Up/Down							
Power On Time (V <sub>DD</sub> ↑), V <sub>OUT</sub> Settles	t <sub>PON</sub>	—	60	—	μs	All	V <sub>DD</sub> = 0V to 4.0V, V <sub>L</sub> = 0V, 90% of V <sub>OUT</sub> change
Power Off Time (V <sub>DD</sub> ↓), V <sub>OUT</sub> Settles	t <sub>POFF</sub>	-	60	—	μs	All	V <sub>DD</sub> = 4.0V to 0V, V <sub>L</sub> = 0V, 90% of V <sub>OUT</sub> change
Step Response							
Inverting Input Overdrive Timing	t <sub>IRDIM</sub>	-	65	—	μs	All	
Noninverting Input Overdrive Timing	t <sub>IRDIP</sub>		85	_	μs	All	
Large Common Mode Step Recovery Time	t <sub>CMS</sub>		70	_	μs	All	10V V <sub>CM</sub> Step

**Note 1:** See Figure 2-33 for the noise density over a wider frequency range.

### TABLE 1-3: TEMPERATURE SPECIFICATIONS

<b>Electrical Characteristics</b> : Unless otherwise indicated, $T_A = +25^{\circ}C$ , $V_{DD} = 5.5V$ , $V_{SS} = GND$ , $V_{CM} = 15V$ , $V_{DM} = 0V$ , $V_{REF} = V_{DD}/2$ , $V_{OUT} = V_{DD}/2$ , $V_L = V_{DD}/2$ , $R_L = 10 \text{ k}\Omega$ and $C_L = 30 \text{ pF}$								
Parameters Sym. Min. Typ. Max. Units Conditions								
Specified Temperature Range	T <sub>A</sub>	-40	—	+125	°C	Note 1		
Operating Temperature Range		-40	_	—		Note 1		
Storage Temperature Range		-60	_	+150		No power		
Thermal Resistance, SC-70	$\theta_{JA}$		209	—	°C/W			

Note 1: Operation must not cause T<sub>J</sub> to exceed the Absolute Maximum Junction Temperature specification (+155°C), which is not intended for continuous use. See Section 4.1.5, Temperature Performance for design tips.

### 1.3 Simplified Diagrams

#### 1.3.1 VOLTAGE RANGE DIAGRAMS

These ranges are constant across temperature.

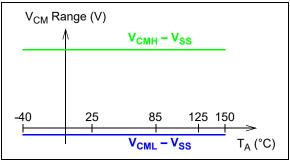
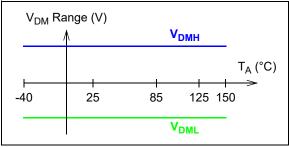


FIGURE 1-1: Common-Mode Input Voltage Range vs. Temperature.



**FIGURE 1-2:** Differential Input Voltage Range vs. Temperature.

#### 1.3.2 TIMING DIAGRAMS

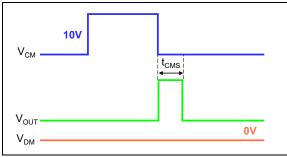


FIGURE 1-3: Large Common-Mode Voltage Step Response.

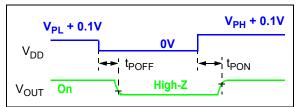


FIGURE 1-4: V<sub>OUT</sub> Power On/Off Timing Diagram.

### 1.4 Simplified Test Circuits

#### 1.4.1 V<sub>OS</sub> TEST CIRCUIT

Figure 1-5 tests the MCP6C26's input offset errors (V<sub>OS</sub>, 1/CMRR, 1/CMRR2 and 1/PSRR etc.). V<sub>OUT</sub> is filtered and amplified, before measuring the result. Note that V<sub>CM</sub> is equal to (V<sub>IP</sub> + V<sub>IM</sub>)/2.

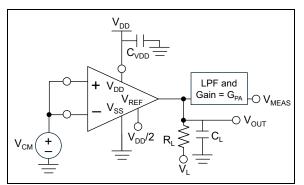


FIGURE 1-5: In the MCP6C26.

Input Offset Test Circuit for

When MCP6C26 is in its normal range of operation, the DC output voltages are (V<sub>E</sub> is the sum of input offset errors and  $g_E$  is the gain error, refer to Equation 1-5):

#### **EQUATION 1-1:**

$$\begin{split} G_{DM} &= \textit{DM Gain} \\ V_{OUT} &= G_{DM}(1+g_E)V_E + V_{REF} \\ V_{MEAS} &= G_{PA}V_{OUT} \end{split}$$

#### 1.4.2 DC DIFFERENTIAL GAIN TEST CIRCUIT

Figure 1-6 is used for testing the differential gain error, nonlinearity and input voltage range (g<sub>E</sub>, INL<sub>DM</sub>, V<sub>DML</sub> and V<sub>DMH</sub>). We compare V<sub>MEAS</sub> with the ideal V<sub>OUT</sub>, then extract the above parameters.

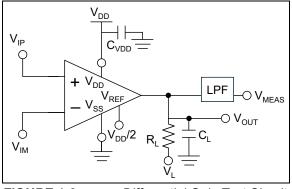


FIGURE 1-6:

Differential Gain Test Circuit.

When measuring the differential input range, all of the voltages must be in range except  $V_{DM}$  ( $V_{DM} = V_{IP} - V_{IM}$ ).

When measuring differential errors ( $g_E$ ,  $\Delta g_E / \Delta T_A$  and INL<sub>DM</sub>), all voltages are held constant, except V<sub>DM</sub>.

#### 1.4.3 AC GAINS TEST CIRCUIT

Figure 1-7 is used for testing the INA's different AC gains. The AC voltages are:

- v<sub>out</sub> is the AC output
- v<sub>cm</sub> is the AC Common-mode input, used for CMRR plots
- v<sub>dm</sub> is the AC differential input, used for G<sub>DM</sub> plots (also for CMRR and PSRR)
- v<sub>dd</sub> and v<sub>ss</sub> are the AC supply inputs, used for PSRR plots (including PSRR+ and PSRR-)
- V<sub>ref</sub> is the AC voltage reference input, used for CMRR2 plots.

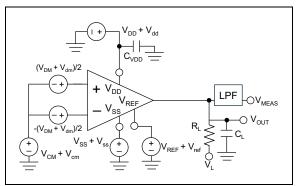


FIGURE 1-7: AC Gain Test Circuit.

#### 1.5 Explanation of DC Error Specifications

#### 1.5.1 LINEAR RESPONSE MODEL

When the inputs and the output are in their normal ranges, and the nonlinear errors are negligible, the output voltage ( $V_{OUT}$ ) is:

#### **EQUATION 1-2:**

$$V_{OUT} = V_{REF} + G_{DM}(1 + g_E)(V_{DM} + V_E)$$

 $V_{DM}$  is the input voltage.  $V_E$  is the sum of input offset errors (due to  $V_{OS}$ , PSRR, CMRR, CMRR2, TC<sub>1</sub>, TC<sub>2</sub>, etc.). g<sub>E</sub> is the gain error (G<sub>DM</sub> is the nominal gain).

#### 1.5.2 INPUT OFFSET RELATED ERRORS

When  $V_{\text{DM}}$  = 0V, the linear response model for  $V_{\text{OUT}}$  becomes:

#### **EQUATION 1-3:**

$$V_{OUT} = V_{REF} + G_{DM}(1 + g_E)V_E$$

The input offset error  $(V_E)$  is extracted from input offset measurements (see Section 1.4.1 "VOS Test Circuit"):

#### **EQUATION 1-4:**

$$V_E = \frac{V_{OUT} - V_{REF}}{G_{DM}(1 + g_E)}$$

It is usually assumed that  $g_E = 0$ , in Equation 1-4, when extracting  $V_E$ . The result is accurate enough, since  $g_E$  is so low.

 $V_{E}$  has several terms, which assume a linear response to changes in  $V_{DD},\,V_{SS},\,V_{CM}$  and  $V_{REF}.$ 

#### **EQUATION 1-5:**

$$V_E = V_{OS} + \frac{\Delta V_{DD} - \Delta V_{SS}}{PSRR} + \frac{\Delta V_{IP}}{CMRR} + \frac{\Delta V_{REF}}{CMRR2} + \Delta T_A TC_1$$

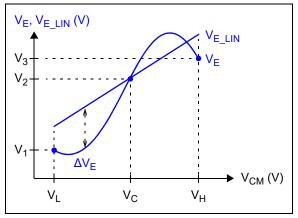
Where:

PSRR, CMRR and CMRR2 are in units of V/V  $\Delta T_A = T_A - 25^{\circ}C$  with units of °C V<sub>DM</sub> = 0

#### 1.5.3 INPUT COMMON-MODE AND DIFFERENTIAL-MODE VOLTAGE NONLINEARITY

The input offset error (V<sub>E</sub>) changes nonlinearly with V<sub>CM</sub>. Figure 1-8 shows the MCP6C26's V<sub>E</sub> vs. V<sub>CM</sub>, as well as a linear fit line (V<sub>E LIN</sub>), that goes through the center point (V<sub>C</sub>, V<sub>2</sub>) and has the same slope as the end points. The nonlinear error is the maximum difference between the two, with the appropriate sign.

The Differential-mode voltage nonlinearity is treated the same way as the Common-mode voltage nonlinearity (i.e., the x-axis becomes  $V_{DM}$ ).

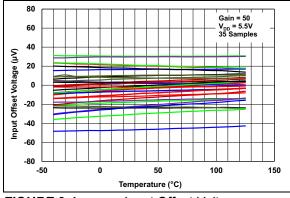


**FIGURE 1-8:** Input Offset Error vs. Common-Mode or Differential-Mode Input Voltage.

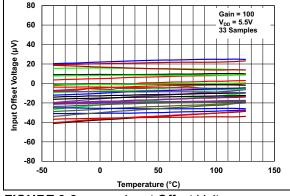
# 2.0 TYPICAL PERFORMANCE CURVES

- **Note:** The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only. The performance characteristics listed herein are not tested or guaranteed. In some graphs or tables, the data presented may be outside the specified operating range (e.g., outside specified power supply range) and therefore outside the warranted range.
- Note: Unless otherwise indicated,  $T_A = +25^{\circ}$ C,  $V_{DD} = 2.7$ V to 5.5V,  $V_{SS} =$ GND,  $V_{CM} = 15$ V,  $V_{DM} = 0$ V,  $V_{REF} = V_{DD}/2$ ,  $V_L = V_{DD}/2$ ,  $R_L = 10 \text{ k}\Omega$  to  $V_L$  and  $C_L = 30 \text{ pF}$ ; see Figure 1-5, Figure 1-6 and Figure 1-7.

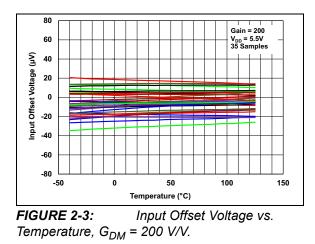
#### 2.1 DC Precision



**FIGURE 2-1:** Input Offset Voltage vs. Temperature,  $G_{DM} = 50$  V/V.



**FIGURE 2-2:** Input Offset Voltage vs. Temperature,  $G_{DM} = 100 \text{ V/V}$ .



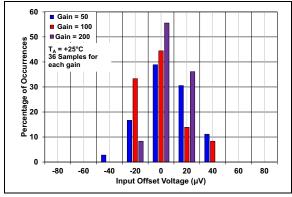


FIGURE 2-4: Input Offset Voltage.

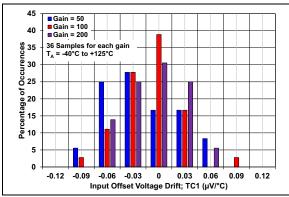
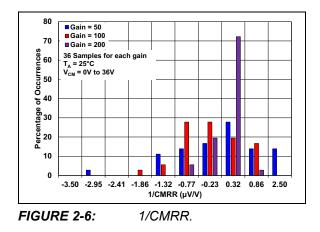
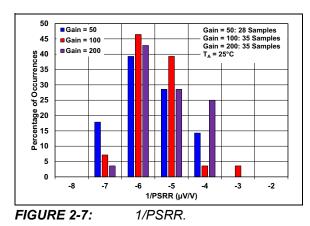


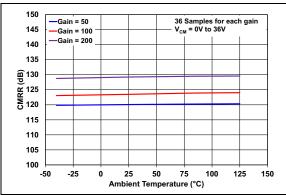
FIGURE 2-5: Linear Input Offset Voltage Drift.

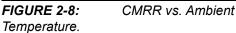


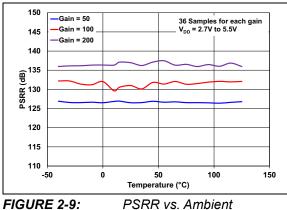
# **MCP6C26**

Note: Unless otherwise indicated,  $T_A = +25^{\circ}C$ ,  $V_{DD} = 2.7V$  to 5.5V,  $V_{SS} = GND$ ,  $V_{CM} = 15V$ ,  $V_{DM} = 0V$ ,  $V_{REF} = V_{DD}/2$ ,  $V_L = V_{DD}/2$ ,  $R_L = 10 \text{ k}\Omega$  to  $V_L$  and  $C_L = 30 \text{ pF}$ ; see Figure 1-5, Figure 1-6 and Figure 1-7.









Temperature.

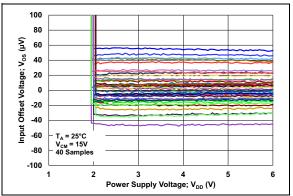
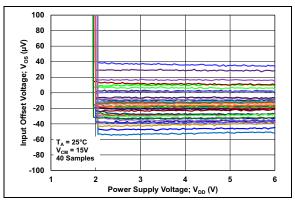
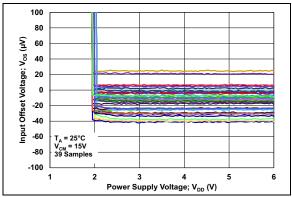


FIGURE 2-10:Input Offset Voltage vs.Power Supply Voltage, with  $G_{DM} = 50$ .



**FIGURE 2-11:** Input Offset Voltage vs. Power Supply Voltage, with  $G_{DM} = 100$ .



**FIGURE 2-12:** Input Offset Voltage vs. Power Supply Voltage, with  $G_{DM} = 200$ .



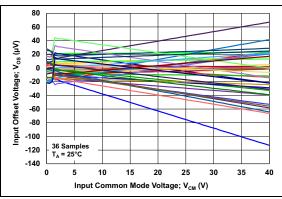
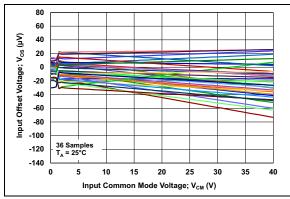
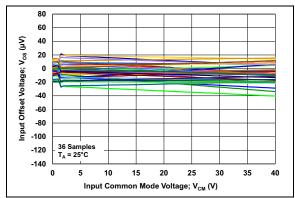


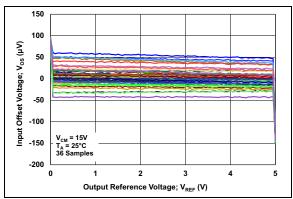
FIGURE 2-13:Input Offset Voltage vs.Common-Mode Input Voltage, with  $G_{DM} = 50$ .



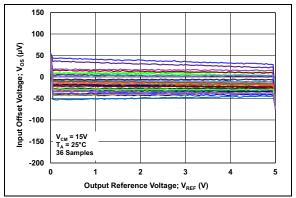
**FIGURE 2-14:** Input Offset Voltage vs. Common-Mode Input Voltage, with  $G_{DM} = 100$ .



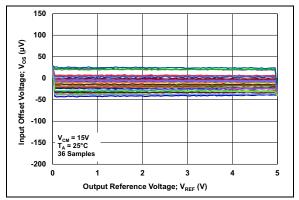
**FIGURE 2-15:** Input Offset Voltage vs. Common-Mode Input Voltage, with  $G_{DM}$  = 200.



**FIGURE 2-16:** Input Offset Voltage vs. Reference Voltage, with  $G_{DM} = 50$ .



**FIGURE 2-17:** Input Offset Voltage vs. Reference Voltage, with  $G_{DM} = 100$ .

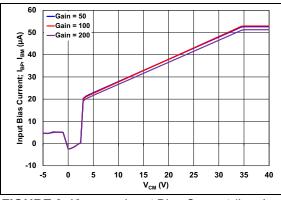


**FIGURE 2-18:** Input Offset Voltage vs. Reference Voltage, with  $G_{DM} = 200$ .

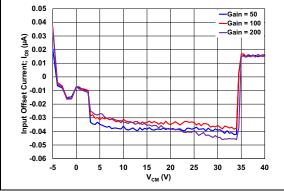
# **MCP6C26**

Note: Unless otherwise indicated,  $T_A = +25^{\circ}C$ ,  $V_{DD} = 2.7V$  to 5.5V,  $V_{SS} = GND$ ,  $V_{CM} = 15V$ ,  $V_{DM} = 0V$ ,  $V_{REF} = V_{DD}/2$ ,  $V_L = V_{DD}/2$ ,  $R_L = 10 \text{ k}\Omega$  to  $V_L$  and  $C_L = 30 \text{ pF}$ ; see Figure 1-5, Figure 1-6 and Figure 1-7.

#### 2.2 Other DC Voltages and Currents



**FIGURE 2-19:** Input Bias Current (I<sub>BP</sub>, I<sub>BM</sub>) vs. Input Common-Mode Voltage.



**FIGURE 2-20:** Input Offset Current (I<sub>OS</sub>) vs. Input Common-Mode Voltage.

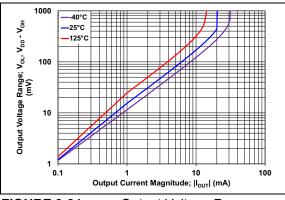


FIGURE 2-21: Output Current.

Output Voltage Range vs.

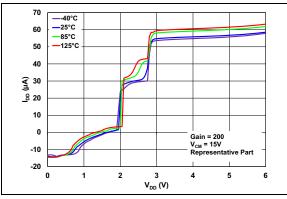


FIGURE 2-22: Supply Current vs. Power Supply Voltage, Ambient Temperature.

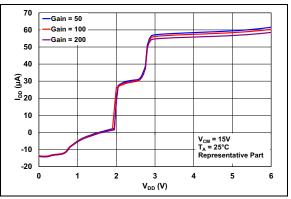
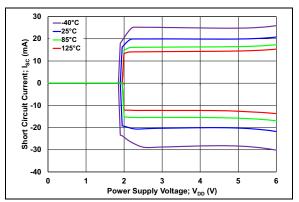


FIGURE 2-23: Supply Current vs. Power Supply Voltage, Gain.



**FIGURE 2-24:** Output Short Circuit Current vs. Power Supply Voltage.



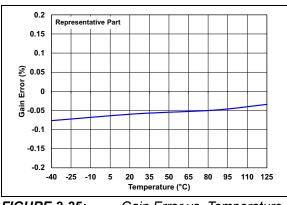


FIGURE 2-25: Ga

Gain Error vs. Temperature.

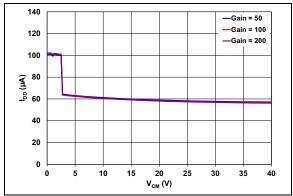


FIGURE 2-26: Supply Current vs. Input Common-Mode Voltage.

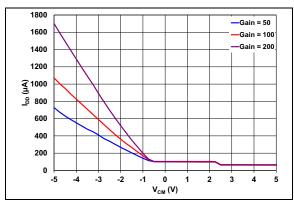
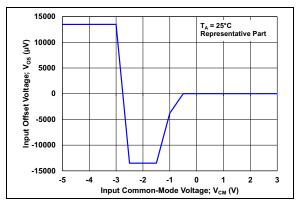


FIGURE 2-27: Supply Current vs. Input Common-Mode Voltage (Survival Region).



**FIGURE 2-28:** Input Offset Voltage vs. Input Common-Mode Voltage (Survival Region).

# **MCP6C26**

Note: Unless otherwise indicated,  $T_A = +25^{\circ}C$ ,  $V_{DD} = 2.7V$  to 5.5V,  $V_{SS} = GND$ ,  $V_{CM} = 15V$ ,  $V_{DM} = 0V$ ,  $V_{REF} = V_{DD}/2$ ,  $V_L = V_{DD}/2$ ,  $R_L = 10 \text{ k}\Omega$  to  $V_L$  and  $C_L = 30 \text{ pF}$ ; see Figure 1-5, Figure 1-6 and Figure 1-7.

#### 2.3 Frequency Response

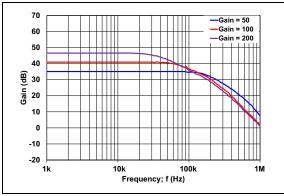


FIGURE 2-29:

Gain vs. Frequency.

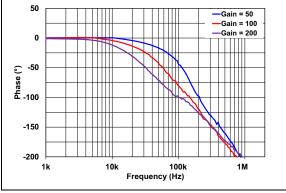


FIGURE 2-30:

Phase vs. Frequency.

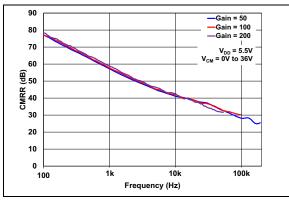
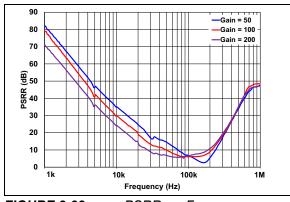


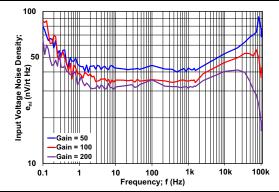
FIGURE 2-31: CMRR vs. Frequency.



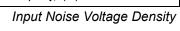


Unless otherwise indicated,  $T_A = +25^{\circ}C$ ,  $V_{DD} = 2.7V$  to 5.5V,  $V_{SS} = GND$ ,  $V_{CM} = 15V$ ,  $V_{DM} = 0V$ ,  $V_{REF} = V_{DD}/2$ ,  $V_L = V_{DD}/2$ ,  $R_L = 10 \text{ k}\Omega$  to  $V_L$  and  $C_L = 30 \text{ pF}$ ; see Figure 1-5, Figure 1-6 and Figure 1-7. Note:

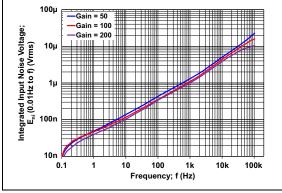
#### 2.4 **Noise and Intermodulation Distortion**



**FIGURE 2-33:** vs. Frequency.









Integrated Input Noise.

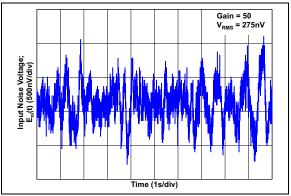


FIGURE 2-35: Input Noise Voltage vs. *Time*,  $G_{DM} = 50$ .

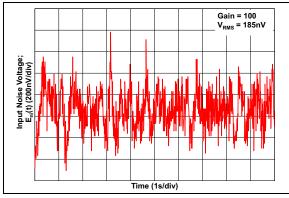
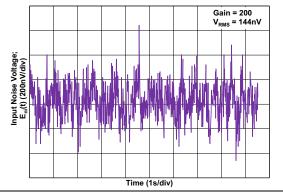


FIGURE 2-36: Input Noise Voltage vs. *Time*,  $G_{DM} = 100$ .

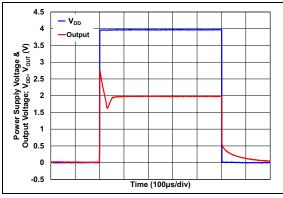


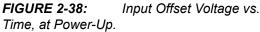
**FIGURE 2-37:** Input Noise Voltage vs. *Time*,  $G_{DM} = 200$ .

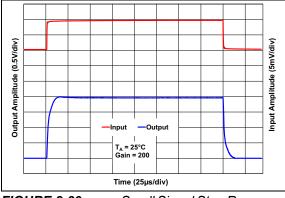
# **MCP6C26**

Note: Unless otherwise indicated,  $T_A = +25^{\circ}C$ ,  $V_{DD} = 2.7V$  to 5.5V,  $V_{SS} = GND$ ,  $V_{CM} = 15V$ ,  $V_{DM} = 0V$ ,  $V_{REF} = V_{DD}/2$ ,  $V_L = V_{DD}/2$ ,  $R_L = 10 \text{ k}\Omega$  to  $V_L$  and  $C_L = 30 \text{ pF}$ ; see Figure 1-5, Figure 1-6 and Figure 1-7.

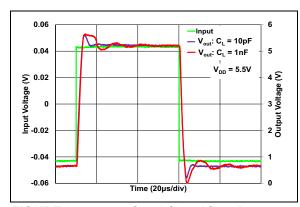
#### 2.5 Time Response







**FIGURE 2-39:** Small Signal Step Response to Differential Input Voltage.



**FIGURE 2-40:** Small Signal Step Response to Differential Input Voltage, with Capacitive Load  $(C_1)$ .

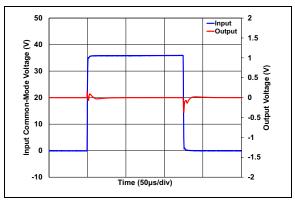
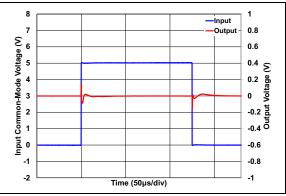
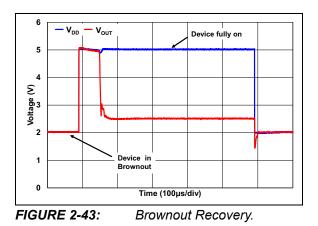


FIGURE 2-41: Input Common Mode Voltage Step Response (36V).



**FIGURE 2-42:** Small Signal Step Response to Common-Mode Input Voltage (5V).



Unless otherwise indicated,  $T_A = +25^{\circ}C$ ,  $V_{DD} = 2.7V$  to 5.5V,  $V_{SS} = GND$ ,  $V_{CM} = 15V$ ,  $V_{DM} = 0V$ ,  $V_{REF} = V_{DD}/2$ ,  $V_L = V_{DD}/2$ ,  $R_L = 10 \text{ k}\Omega$  to  $V_L$  and  $C_L = 30 \text{ pF}$ ; see Figure 1-5, Figure 1-6 and Figure 1-7. Note:

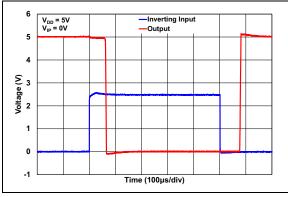
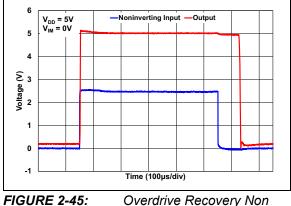


FIGURE 2-44: **Overload Recovery** Inverting.



Inverting.



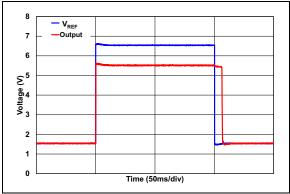


FIGURE 2-46: Overdrive.

Reference Voltage

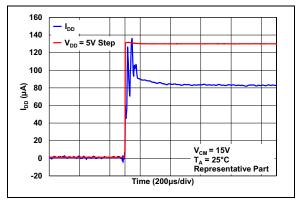


FIGURE 2-47: Supply Current During Power Up.

# 3.0 PIN DESCRIPTIONS

The descriptions of the pins are listed in Table 3-1.

#### TABLE 3-1: PIN FUNCTION TABLE

MCP6C26 SC-70	Sym.	Description					
1	V <sub>OUT</sub>	Output voltage					
2	$V_{SS}$	Negative power supply					
3	V <sub>IP</sub>	Noninverting input (at load's R <sub>SH</sub> ) and positive (high-side) power supply					
4	V <sub>IM</sub>	Inverting input (at load's R <sub>SH</sub> )					
5	$V_{REF}$	Output reference					
6	$V_{DD}$	Positive (low-side) power supply					

# 3.1 Noninverting and Inverting Analog Signal Input (V<sub>IP</sub> and V<sub>IM</sub>)

The noninverting and inverting inputs (V<sub>IP</sub> and V<sub>IM</sub>) drive a resistor connected to the internal op amp. They are designed to operate over a wide voltage range, with a voltage source to drive it. The difference in voltage V<sub>DM</sub> (or V<sub>IP</sub> - V<sub>IM</sub>) is the input signal for this amplifier. The Common-mode voltage V<sub>CM</sub> (or (V<sub>IP</sub> + V<sub>IM</sub>)/2) is rejected by this amplifier.

# 3.2 Analog Output Reference Voltage (V<sub>REF</sub>)

The analog output reference voltage drives a resistor connected to the internal op amp.  $V_{REF}$  is set to a DC voltage, which shifts  $V_{OUT}$ .

### 3.3 Analog Output (V<sub>OUT</sub>)

The analog output pin  $(\mathrm{V}_{\mathrm{OUT}})$  is a low-impedance voltage source.

# 3.4 Low-Side Power Supplies (V<sub>DD</sub>, V<sub>SS</sub>)

 $V_{DD}$  is normally between  $V_{SS}$  + 2.7V and  $V_{SS}$  + 5.5V, while the  $V_{REF}$  and  $V_{OUT}$  pins are usually between  $V_{SS}$  and  $V_{DD}$ .  $V_{DD} - V_{SS}$  triggers the LV POR.

Typically, these parts are used in a single (positive) supply configuration. In this case,  $V_{SS}$  is connected to ground and  $V_{DD}$  is connected to the supply.  $V_{DD}$  will need good bypass capacitors.

In split supply configurations, including dual supplies, ground is between  $V_{SS}$  and  $V_{DD}.$  Both supply pins will need good bypass capacitors.

In a single (negative) supply configuration,  $V_{DD}$  connects to ground and  $V_{SS}$  connects to the supply.  $V_{SS}$  will need good bypass capacitors.

### 4.0 DEVICE OPERATION

This chapter includes additional information on basic operations and major functions.

#### 4.1 Basic Performance

#### 4.1.1 IDEAL PERFORMANCE

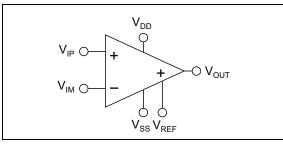
Figure 4-1 shows the basic circuit; inputs, supplies and output. When the inputs ( $V_{IP}$ ,  $V_{IM}$ ,  $V_{DD}$ ,  $V_{SS}$  and  $V_{REF}$ ) and output ( $V_{OUT}$ ) are in their specified ranges, and the part is nearly ideal, the output voltage is:

#### **EQUATION 4-1:**

$$V_{OUT} \approx V_{REF} + G_{DM} V_{DM}$$

Where:

- G<sub>DM</sub> = Differential-Mode Gain
- V<sub>REF</sub> = Output Reference Voltage
- $V_{DM}$  = Differential-Mode Input ( $V_{IP} V_{IM}$ )



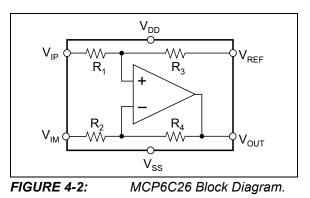


For normal operation, keep:

- +  $V_{CM}$  between  $V_{CML}$  and  $V_{CMH}$
- $V_{DM}$  between  $V_{DML}$  and  $V_{DMH}$
- $V_{REF}$  between  $V_{RL}$  and  $V_{RH}$
- + V<sub>OUT</sub> between 0.1V to V<sub>DD</sub> 0.1V, usually V<sub>OL</sub> and V<sub>OH</sub> are hard limits

#### 4.1.2 ANALOG ARCHITECTURE

Figure 4-2 shows the block diagram for these current sense amplifiers.



#### 4.1.3 DC PERFORMANCE

#### 4.1.3.1 DC Voltage Errors

Section 1.5, Explanation of DC Error Specifications covers some DC specifications. The input offset error (with temperature coefficients), gain error and nonlinearities are discussed in detail.

#### 4.1.3.2 DC Current Errors

Figure 4-3 shows the resistors and currents that change the DC bias point. The input bias currents ( $I_{BP}$ ,  $I_{BM}$  and  $I_{BR}$ ), together with a circuit's external input resistances, give a DC error (see Section 1.4.2, DC Differential Gain Test Circuit).

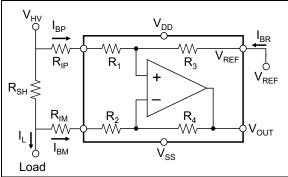


FIGURE 4-3: DC Bias Resistors and Currents.

 $R_{SH}$  is set by the design requirements, given the load current (I<sub>L</sub>). For most applications,  $R_{SH}$  would be between 100  $\mu\Omega$  and 1 $\Omega$ . Keep  $R_{IP}$  and  $R_{IM}$  below 10 $\Omega$  to minimize input offset errors.

The DC input offset error due to the input currents is:

$$V_{OS_{IR}} = V_{DM} - I_L R_{SH}$$
$$= I_{BM} (R_{SH} + R_{WIM}) - I_{BP} R_{WIP}$$

#### 4.1.4 AC PERFORMANCE

The Gain-Bandwidth Products of these parts (GBWP) is set internally to 9MHz; divide by the gain to obtain the small signal bandwidth (BW). The Bandwidth at the maximum output swing is called the Full Power Bandwidth (FPBW), which is limited either by the BW or by the Slew Rate (SR). To estimate the FPBW for sine waves, use this approximate formula:

FPBW  $\approx$  min(BW, SR/( $\pi$  V<sub>PP</sub>)), V<sub>PP</sub> = the peak-to-peak magnitude of V<sub>OUT</sub>

These parts are compensated to have a stable response. For instance, step response overshoot is low.

#### 4.1.5 TEMPERATURE PERFORMANCE

The input offset voltage's temperature drift is detailed in Equation 1-5. Other temperature responses are shown in Section 1.2, Specifications and Section 2.0 "Typical Performance Curves".

Since there are three power supply pins (V<sub>IP</sub>, V<sub>DD</sub> and V<sub>SS</sub>), and V<sub>IP</sub> reaches 36V, power and temperature rise calculations are important.

The power dissipated is calculated as follows (I\_{OUT} is positive when it flows out of the V\_{OUT} pin):

#### **EQUATION 4-2:**

$$P_{TOT} = P_{DD} + P_{BM} + P_{BP} + P_{OUT}$$

Where:

$R_1$	=	20k, 10k, 5k (Note 1)
$R_2$	=	20k, 10k, 5k (Note 1)
$R_3$	=	1 MΩ (Note 1)
$R_4$	=	1 MΩ (Note 1)
I <sub>OUT</sub>	=	(V <sub>OUT</sub> - V <sub>L</sub> )/R <sub>L</sub>
$P_{DD}$	=	(V <sub>DD</sub> - V <sub>SS</sub> ) I <sub>DD</sub>
$P_{BM}$		(V <sub>IM</sub> - V <sub>REF</sub> ) <sup>2</sup> /(R <sub>2</sub> + R <sub>4</sub> )
$P_{BP}$	=	(V <sub>IP</sub> - V <sub>REF</sub> ) <sup>2</sup> /(R <sub>1</sub> + R <sub>3</sub> )
P <sub>OUT</sub>	=	(V <sub>DD</sub> - V <sub>OUT</sub> ) I <sub>OUT</sub> , I <sub>OUT</sub> ≥ 0A
	=	(V <sub>SS</sub> - V <sub>OUT</sub> ) I <sub>OUT</sub> , I <sub>OUT</sub> < 0A

Note 1:	See DC E	lectrical	Characteristics for the				
	respective	gains	for each		resistance.		
	These are typical values only.						

Now we can estimate the junction temperature of the device (see Table 1-3):

#### **EQUATION 4-3:**

$$T_J = T_A + P_{TOT}\theta_{JA}$$

#### 4.1.6 NOISE PERFORMANCE

This part is designed to have low input noise voltage density at lower frequencies. The offset correction modulates low frequency 1/f noise to higher frequencies.

The measured input noise voltage density is shown in Figure 2-33. Figure 2-34 also shows Integrated Input Noise Voltage ( $E_{ni}$ , in units of  $V_{RMS}$ ) between 0 Hz and f (between 0.1 Hz and 100 kHz).

#### 4.1.7 FINAL TEST VS. BENCH

Final test measurements are not as accurate as bench measurements. For this reason, the input offset voltage related specifications ( $V_{OS}$ ,  $TC_1$ , ..., CMRR and PSRR) are significantly wider than the histograms from bench measurements.

The bench results will give good guidance on how to design your circuit. The specified limits (for final test) give min/max limits used to screen outliers in production.

# 4.1.8 INTERMODULATION DISTORTION (IMD)

These amplifiers will show intermodulation distortion (IMD) products when an AC signal is present.

The signal and clock can be decomposed into sine wave tones (Fourier series components). These tones interact with the zero-drift circuitry's nonlinear response to produce IMD tones at sum and difference frequencies. Each of the square wave clock's harmonics has a series of IMD tones centered on it. These effects can be minimized by reducing external signals that cause intermodulation.

### 4.2 Internal Protection

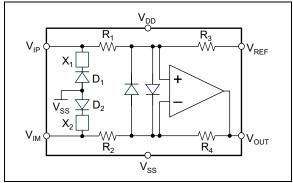
The MCP6C26 helps the designer provide enough protection against undesired conditions and signals in their environment.

#### 4.2.1 INTERNAL PROTECTION DEVICES

All of the ESD structures clamp their inputs when they try to go too far below  $V_{SS}$ . Their breakdown voltage is high enough to allow normal operation, but not low enough to protect against slow overvoltage events. Very fast ESD events (that meet the specification) are limited so that damage does not occur.

The supply inputs ( $V_{DD}$  -  $V_{SS}$ ) are also connected to PORs, so that internal power-up sequencing is well controlled.

The V<sub>IP</sub> and V<sub>IM</sub> input pins have an ESD structure (D1, D2, X1, X2) designed to limit V<sub>IP</sub> - V<sub>SS</sub>, V<sub>IM</sub> - V<sub>SS</sub> and V<sub>DM</sub>. If either V<sub>IP</sub> or V<sub>IM</sub> go too high, they exceed a breakdown voltage and clamp. If either one goes too low (e.g., -5V), the current at the inputs is limited.



**FIGURE 4-4:** Input Protection for  $V_{IP}$ ,  $V_{IM}$  and  $V_{DM} = V_{IP} - V_{IM}$ .

The V<sub>REF</sub>, V<sub>OUT</sub> and V<sub>DD</sub> pins have ESD structures that limit their voltages when they try to go too far below V<sub>SS</sub> (i.e., limit V<sub>REF</sub> - V<sub>SS</sub>, V<sub>OUT</sub> - V<sub>SS</sub> and V<sub>DD</sub> - V<sub>SS</sub>).

#### 4.2.2 PHASE REVERSAL

This part is designed to not exhibit phase inversion when the input signals (V<sub>CM</sub>, V<sub>DM</sub> and V<sub>REF</sub>) exceed their specified ranges.

# 5.0 APPLICATIONS

This chapter includes design recommendations and typical application circuits.

The Common-mode rejection (see Figure 2-13, Figure 2-14, Figure 2-15 and Figure 2-32) supports high accuracy applications in noisy environments.

The power supply rejection (see Figure Note:) also has excellent rejection at higher frequencies than traditional.

#### 5.1 Recommended Design Practices

Some simple design practices help take advantage of the MCP6C26's performance in high-side current sensing applications.

#### 5.1.1 SAFETY PRECAUTIONS

Since the MCP6C26 is used in circuits with voltages and currents that can be hazardous to humans, appropriate cautions need to be observed when designing and using said circuits. Please refer to the appropriate industry and government standards and laws to determine design and usage practices.

#### 5.1.2 INPUT VOLTAGE/CURRENT LIMITS

To prevent damage and/or improper operation of these amplifiers, the circuit must limit the voltages and currents at and into the V<sub>IP</sub> and V<sub>IM</sub> input pins, as well as the differential input voltage V<sub>DM</sub> (see Section 1.1, Absolute Maximum Ratings †). Note that the voltage limits are independent of the current limits and need separate attention to ensure these limits.

The ESD protection on the V<sub>CM</sub> and V<sub>DM</sub> inputs was discussed in **Section 4.2.1**, **Internal Protection Devices**. This structure was chosen to protect the input transistors against many (but not all) overvoltage conditions, and to minimize input bias currents (I<sub>BP</sub> and I<sub>BM</sub>).

To protect the inputs, always drive V<sub>IP</sub> with a low impedance source and use a shunt resistor (R<sub>SH</sub>) with low resistance (designed to not fail open). Placing zener diode(s) or a transorb across R<sub>SH</sub> will also help protect the inputs.

#### 5.1.3 BYPASS CAPACITORS

Be sure to specify capacitors that will support your application. Be sure to look at:

- Voltage Rating (well above the maximum value at each pin)
- Dielectrics (good Temp. Cos. and reasonable Volt. Cos.)
- Size
- Surface Mount vs. Leaded
- · Cost vs. availability

If possible, connect  $\mathsf{V}_{\mathsf{SS}}$  to ground. This will make your design simpler.

For both positive and negative single power supply configurations, bypass  $V_{DD}$  to  $V_{SS}$  with a local bypass capacitor next to these pins (e.g., 100 nF). A bulk bypass capacitor should also be added close by (e.g., 2.2  $\mu$ F); placing it next to the local bypass capacitor is a good choice.

For dual power supply configurations, bypass  $V_{DD}$  and  $V_{SS}$  to ground separately with a local bypass capacitor next to these pins. A bulk bypass capacitor should also be added close by; placing it next to the local bypass capacitor is a good choice.

#### 5.1.4 PROTECTING THE INPUTS IN HIGH-SIDE CURRENT SENSING APPLICATIONS

Designs using the MCP6C26 will need protection methods in the circuit design. When working on the bench, be careful to use the same protection methods (e.g., do not hot-swap the supply voltages). The following subsections give ideas that may be useful in your design.

#### 5.1.4.1 Protecting $V_{DM}$ ( $V_{IP}$ - $V_{IM}$ )

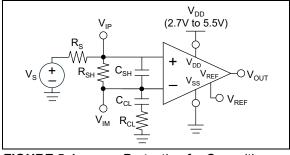
The shunt resistor ( $R_{SH}$  in Figure 5-1 keeps  $V_{DM}$  in range, as long as the load current is not too high. If extra protection is needed in your design, ideas to consider include:

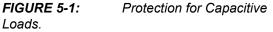
- Limiting V<sub>S</sub>'s output current
- Setting V<sub>S</sub>'s output ESR high enough to reduce overshoot
  - The ESR should be a dynamic resistance, not a physical one.

#### 5.1.4.2 Protection for Capacitive Loads

Capacitive loads pass large currents when their voltage changes fast (e.g., at start-up or power down). These currents will cause voltage drops across resistors and (parasitic) inductors in the current path. The voltage drop across inductors can be substantial.

Limiting the current from V<sub>S</sub> helps protect the circuit in Figure 5-1. The resistance seen by V<sub>S</sub> (R<sub>S</sub> (V<sub>S</sub>'s ESR) and R<sub>CL</sub> (C<sub>CL</sub>'s ESR) helps reduce step response overshoot, which provides more protection. Using C<sub>SH</sub> will create a voltage divider for fast edges; be careful to limit the resulting V<sub>DM</sub>.





#### 5.1.4.3 Protection for Motor Loads

Motor loads are inductive, with resistance and feedback voltage (back EMF) effects. They will generate large voltages when their currents change fast (e.g., at start-up or power down). These voltages will cause currents to flow through resistors, inductors and (parasitic) capacitors in the current path. The currents through capacitors can be substantial.

Limiting the current and/or edge rates from V<sub>S</sub> helps protect the circuit in Figure 5-2. The resistance  $R_S$ (V<sub>S</sub>'s ESR) might help in some designs. The catch diode (D<sub>1</sub>) keeps the motor voltage from going too far below ground, which protects the inputs.

Overvoltage events at  $V_S$  need to be limited. Current from  $V_S$  can be limited to one direction with a forward-biased diode between  $V_S$  and  $V_{IP}$ .

Elements in parallel to the motor can help protect the components. For DC protection, a forward-biased diode and series resistor may help. For AC protection, a capacitor may help. Varistors can help too.

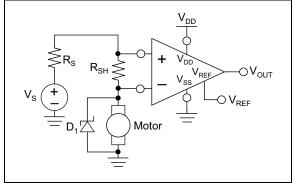


FIGURE 5-2:

Protection for Motor Loads.

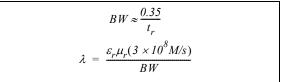
#### 5.1.4.4 Protection From Long Line (Wire) Effects

Long wires between the source ( $V_S$ ) and MCP6C26 to the load can cause issues in some applications. These issues include capacitive loading and transmission line effects.

The wire capacitance acts in parallel to the load, when the frequency content to the load is relatively slow. If the load is light, this can be a significant effect. The protections for capacitive loads can also be used here.

The wire acts as a transmission line when the frequency content to the load is relatively fast. The highest frequency of interest in a PWM waveform is related to the edges' rise and fall times  $(t_r)$  and their equivalent bandwidth (BW). The relative permittivity  $(\epsilon_r)$  and relative permeability  $(\mu_r)$  of the PCB modify the wavelength  $(\lambda)$ . The wavelength is then estimated as:

#### **EQUATION 5-1:**

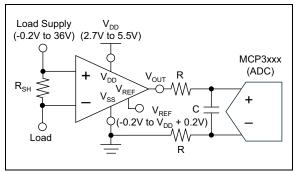


The wire's length should be less than  $\lambda$ /10. When that is not the case, there are several possible remedies, such as:

- Placing a filter at the load to limit BW (increase t<sub>r</sub>)
- Placing a series R-C snubber in parallel with the load
- Limiting rise and fall times at the source (V<sub>S</sub>).

#### 5.1.5 SETTING THE VOLTAGE AT V<sub>REF</sub>

Ensure that Load supply,  $\mathsf{V}_{DD},\,\mathsf{V}_{SS}$  and  $\mathsf{V}_{REF}$  remain within specified limits.





V<sub>RFF</sub> Bypass Circuit #1.

Figure 5-3 uses an IC V<sub>REF</sub> to generate V<sub>REF</sub> - V<sub>SS</sub>, an R-C low pass filter to reject fast glitches seen at V<sub>REF</sub> - V<sub>SS</sub> and an op amp buffer ( $\geq$  1 MHz) to drive V<sub>REF</sub> with a low impedance source (notice only one connection to V<sub>SS</sub> is shown, for good precision).

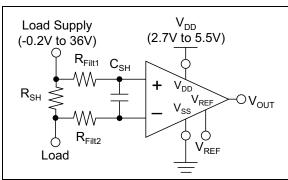
#### 5.1.6 INPUT FILTERING

Figure 5-4 depicts input filter connections. The series input resistors should not exceed  $10\Omega$ , and companion capacitor values determined accordingly. Input filtering may be required for any or all of these reasons:

- 1. An inherently noisy current signal,
- 2. The effects of shunt inductance,
- 3. To avoid aliasing in the chopper stabilized amplifier if there is considerable signal content near the zero-drift switching frequency of 200 kHz, or
- 4. To reduce effects of fast transients.

It is also possible to filter noise at the output of the MCP6C26 (assuming the amplitude of the noise is low enough to not cause overloading within the MCP6C26).

The inductance of low value shunts causes a rise in high-frequency response at surprisingly low frequencies (e.g. 10 kHz to 20 kHz), accentuating high-frequency components, including fast transients. In some cases, this high-frequency content can worsen signals at the output.





#### 5.1.7 TEMPERATURE RISE

Make sure that  $T_J$  does not exceed the Absolute Maximum Junction Temperature spec (see Section 1.1, Absolute Maximum Ratings †). This is a strong concern when  $T_A$  is high (e.g., at +125°C) and when  $I_{OUT}$ 's magnitude is large (e.g., near the short circuit limit) or when  $V_{IP}$  is high.

Formulas needed for this part of the design are found in **Section 4.1.5, Temperature Performance**.

#### 5.1.8 ENSURING STABILITY

A few simple design techniques will help take advantage of these stable parts. Simulations and bench measurements help to verify the solutions (e.g., look at step response overshoot and ringing).

#### 5.1.8.1 Driving V<sub>REF</sub>

The voltage source driving the  $V_{REF}$  pin must be low impedance (see Section 5.1.6, Input Filtering), throughout the MCP6C26's bandwidth, so that the signal gain is constant within the signal bandwidth.

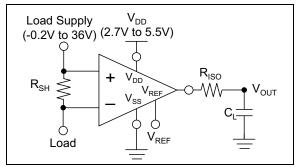
#### 5.1.8.2 Source Impedances

The recommended DC source resistances (at V<sub>IP</sub>, V<sub>IM</sub> and V<sub>REF</sub>; see Section 5.1.6, Input Filtering) will help ensure stability, by keeping R-C time constants very fast.

#### 5.1.8.3 Capacitive Loads

Driving large capacitive loads can cause stability problems for voltage amplifiers. As the load capacitance increases, the feedback loop's phase margin decreases. This produces gain peaking in the frequency response, with overshoot and ringing in the step response. Sensitivity to capacitive loads also changes with gain ( $G_{DM}$ ).

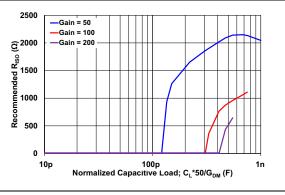
When driving large capacitive loads with these parts, a small series resistor at the output ( $R_{ISO}$  in Figure 5-5) improves the feedback loop's phase margin (stability) by making the output load resistive at higher frequencies. The bandwidth will be generally lower than the bandwidth with no capacitive load.



**FIGURE 5-5:** Include R<sub>ISO</sub> with Capacitive Loads to Improve Phase Margin.

Figure 5-6 gives recommended  $R_{ISO}$  values for different capacitive loads and gains. The x-axis is the normalized (by 50/G<sub>DM</sub>) load capacitance (C<sub>L</sub>).

After selecting  $R_{ISO}$  for the circuit, double check the resulting frequency response peaking and step response overshoot on the bench. Modify  $R_{ISO}$ 's value until the response is reasonable.



*FIGURE 5-6:* Recommended R<sub>ISO</sub> vs. Capacitive Load.

#### 5.1.9 UNIDIRECTIONAL APPLICATIONS

In unidirectional applications where V<sub>REF</sub> = V<sub>SS</sub>, it is important to minimize output headroom (V<sub>OL</sub>). The lower V<sub>OL</sub> is, the more accurate the zero scale reading is. This is done by making R<sub>L</sub> high and by tying V<sub>L</sub> to V<sub>SS</sub>.

In unidirectional applications where V<sub>REF</sub> = V<sub>DD</sub>, it is important to minimize output headroom (V<sub>DD</sub> - V<sub>OH</sub>). The higher V<sub>OH</sub> is, the more accurate the zero scale reading is. This is done by making R<sub>L</sub> high and by tying V<sub>L</sub> to V<sub>DD</sub>.

Figure 5-3 shows how to connect  $\mathsf{V}_{\mathsf{REF}}$  and  $\mathsf{V}_{\mathsf{SS}}$  for best performance.

#### 5.1.10 BIDIRECTIONAL APPLICATIONS

To maximize headroom, reduce  $V_{OL}$  and  $V_{OH}$  by setting  $R_L$  high and by setting  $V_L$  to mid-supply.

#### 5.1.11 SUPPLY PINS

See Section 3.4, Low-Side Power Supplies (VDD, VSS) for common power supply pin design approaches.

Setting  $V_{SS}$  = GND has the potential to increase rejection of crosstalk and glitches. In any case, a good ground design (e.g., ground plane on a PCB) and appropriate bypass capacitors are needed to realize these benefits. It pays to be sure that your capacitor's voltage rating and dielectric will support your needs over your voltage and temperature ranges. With some dielectrics, it pays to also take aging (changes over time) into account too.

#### 5.1.12 PCB TIPS

These amplifiers are specified up to 36V at the  $V_{IP}$  pin and the load currents can be high. For these reasons, the PCB design needs to be done with care.

Industry standards, such as IPC-2221A, give requirements for many PCB related topics. These topics include current capacity of traces, spacing between conductors, altitude effects, coatings and parasitic impedances.

A package's pin spacing, together with other design choices, affects the maximum voltage allowed between adjacent pins.

#### 5.1.13 OTHER APPLICATIONS

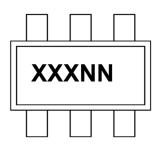
Other applications not related to high-side current sensing that the MCP6C26 can be used for are:

- · Low-side current sensing
- Differential sensor conditioning.

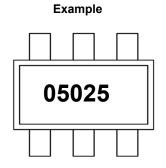
# 6.0 PACKAGING INFORMATION

# 6.1 Package Marking Information

6-Lead SC70



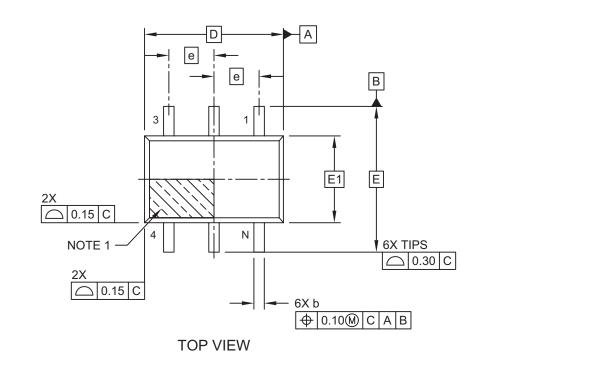
Part Number	Code
MCP6C26T-050E/LTY	050NN
MCP6C26T-100E/LTY	100NN
MCP6C26T-200E/LTY	200NN

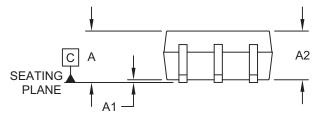


Legend:	XXX Y YY WW NNN (e3) *	Device-specific information Year code (last digit of calendar year) Year code (last 2 digits of calendar year) Week code (week of January 1 is week '01') Alphanumeric traceability code Pb-free JEDEC designator for Matte Tin (Sn) This package is Pb-free. The Pb-free JEDEC designator ((e3)) can be found on the outer packaging for this package.
	be carrie	nt the full Microchip part number cannot be marked on one line, it will d over to the next line, thus limiting the number of available s for customer-specific information.

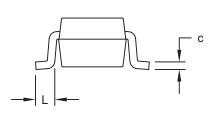
## 6-Lead Plastic Small Outline Transistor (D4A) - 2.0x1.25mm Body [SC70]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging





SIDE VIEW

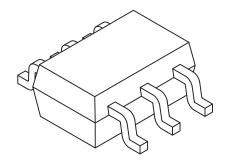


END VIEW

Microchip Technology Drawing C04-1133C Sheet 1 of 2

# 6-Lead Plastic Small Outline Transistor (D4A) - 2.0x1.25mm Body [SC70]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	MILLIMETERS					
Dimension	Dimension Limits					
Number of Pins	N		6			
Pitch	е		0.65 BSC			
Overall Height	A	0.80	-	1.10		
Standoff	A1	0.00	-	0.10		
Molded Package Thickness	A2	0.80	0.90	1.00		
Overall Length	D		2.00 BSC			
Exposed Pad Length	D2	2.50	2.60	2.70		
Overall Width	E		2.10 BSC			
Exposed Pad Width	E1	1.25 BSC				
Terminal Width	b	0.15	-	0.30		
Terminal Length	L	0.10	0.20	0.46		
Lead Thickness	С	0.08	-	0.22		

#### Notes:

1. Pin 1 visual index feature may vary, but must be located within the hatched area.

2. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.15mm per side.

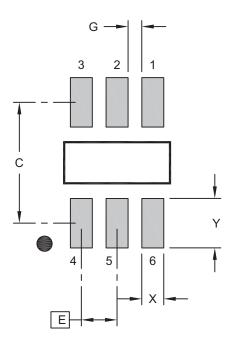
3. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances. REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing C04-1133C Sheet 2 of 2

### 6-Lead Plastic Small Outline Transistor (D4A) - 2.0x1.25mm Body [SC70]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



# RECOMMENDED LAND PATTERN

	MILLIMETERS			
Dimension	MIN	NOM	MAX	
Contact Pitch	E	0.65 BSC		
Contact Pad Spacing	С		1.90	
Contact Pad Width (X6)	Х			0.42
Contact Pad Length (X6)	Y			0.77
Distance Between Pads	G	0.23		

Notes:

1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing C04-3133C

# **MCP6C26**

NOTES:

# APPENDIX A: REVISION HISTORY

### Revision B (March 2025)

- Updated Table 1-1.
- Updated Section 2.5, Time Response.

# **Revision A (September 2024)**

• Initial release of this document.

# **PRODUCT IDENTIFICATION SYSTEM**

To order or obtain information, e.g., on pricing or delivery, refer to the factory or the listed sales office.

PART NO.   Device Ta	[X] <sup>(1)</sup>   pe and Red Option	-XXX   el Gain Option	X Temperature Range	/XXX   Package	Example a) MCP6	<b>'S:</b> C26T-050E/LTY:	Tape and Reel, Differential Gain = 50, Extended Temperature,	
Device:	MCP6C2 Amplifier	6: 36V High and I	_ow-Side Currer	nt Sense Difference	b) MCP60	C26T-100E/LTY:	6LD SC70 Tape and Reel, Differential Gain = 100, Extended Temperature, 6LD SC70	
Tape and Reel Option:	T =	Tape and Reel <sup>(1)</sup>			c) MCP60	C26T-200E/LTY:	Tape and Reel, Differential Gain = 200, Extended Temperature, 6LD SC70	
Gain Option:	100 =	Differential Gain o Differential Gain o Differential Gain o	f 100 V/V					
Temperature Range:	E =	-40°C to +125°C	(Extended)		Note 1:	Tape and Reel identifier only appears in the catalog part number description. This identifier is used for ordering purposes and is not printed on		
Package:	LTY =	Plastic Small Out 6-Lead Nickel-Pa					e. Check with your Microchip ckage availability with the Tape	

# **MCP6C26**

NOTES:

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